

# MOSFET - Power, Single P-Channel

## -40 V, 9.5 mΩ, -77 A

### NVMFS9D6P04M8L

#### Features

- Small Footprint for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- NVMFWS9D6P04M8L – Wettable Flanks Product
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR-Free and are RoHS Compliant

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	$V_{DSS}$	-40	V	
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V	
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 4)	Steady State	$T_C = 25^\circ\text{C}$	$I_D$ -77.0	A
		$T_C = 100^\circ\text{C}$	-54.4	
Power Dissipation $R_{\theta JC}$ (Notes 1, 2)	Steady State	$T_C = 25^\circ\text{C}$	$P_D$ 75	W
		$T_C = 100^\circ\text{C}$	38	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3, 4)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$ -17.1	A
		$T_A = 100^\circ\text{C}$	-12.1	
Power Dissipation $R_{\theta JA}$ (Notes 1, 3)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$ 3.7	W
		$T_A = 100^\circ\text{C}$	1.8	
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	$I_{DM}$ 450	A	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)	$I_S$	-62	A	
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = -8.5 \text{ A}$ )	$E_{AS}$	259	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

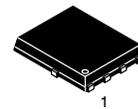
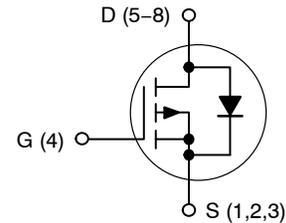
#### THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Drain) (Notes 1, 2, 4)	$R_{\theta JC}$	2	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	40.7	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Assumes heat-sink sufficiently large to maintain constant case temperature independent of device power.
3. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
4. Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

$V_{(BR)DSS}$	$R_{DS(on) MAX}$	$I_D MAX$
-40 V	9.5 mΩ @ -10 V	-77 A
	13.8 mΩ @ -4.5 V	

#### P-Channel MOSFET



DFN5 (SO-8FL)  
STYLE 1  
CASE 488AA

#### MARKING DIAGRAM



XXXXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
W = Work Week  
ZZ = Lot Traceability

#### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

# NVMFS9D6P04M8L

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>			21		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -40 V	T <sub>J</sub> = 25°C		-1.0	μA
			T <sub>J</sub> = 125°C		-1000	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA

### ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = -580 μA	-1.0		-2.4	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>			-5.1		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -20 A		7.15	9.5	mΩ
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -10 A		10.4	13.8	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -1.5 V, I <sub>D</sub> = -15 A		36		S

### CHARGES AND CAPACITANCES

Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = -20 V		2002		pF
Output Capacitance	C <sub>oss</sub>			935		
Reverse Transfer Capacitance	C <sub>rss</sub>			43		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>DS</sub> = -20 V, I <sub>D</sub> = -20 A	V <sub>GS</sub> = -4.5 V	15.04		nC
			V <sub>GS</sub> = -10 V	14.47		
Threshold Gate Charge	Q <sub>G(TH)</sub>	V <sub>GS</sub> = -10 V, V <sub>DS</sub> = -20 V, I <sub>D</sub> = -20 A		4.27		nC
Gate-to-Source Charge	Q <sub>GS</sub>			11.94		
Gate-to-Drain Charge	Q <sub>GD</sub>			12.83		
Plateau Voltage	V <sub>GP</sub>			3.63		

### SWITCHING CHARACTERISTICS, V<sub>GS</sub> = -4.5 V (Note 6)

Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -20 V, I <sub>D</sub> = -20 A, R <sub>G</sub> = 2.5 Ω		13.1		ns
Rise Time	t <sub>r</sub>			103		
Turn-Off Delay Time	t <sub>d(off)</sub>			83.3		
Fall Time	t <sub>f</sub>			63.0		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -20 A	T <sub>J</sub> = 25°C	-0.86	-1.25	V
			T <sub>J</sub> = 125°C	-0.74		
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs, I <sub>S</sub> = -20 A		54.6		ns
Charge Time	t <sub>a</sub>			34.9		
Discharge Time	t <sub>b</sub>			19.7		
Reverse Recovery Charge	Q <sub>RR</sub>			97.9		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

# NVMFS9D6P04M8L

## TYPICAL CHARACTERISTICS

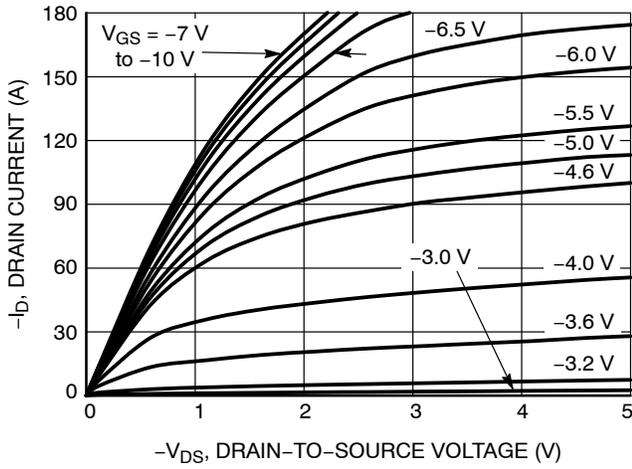


Figure 1. On-Region Characteristics

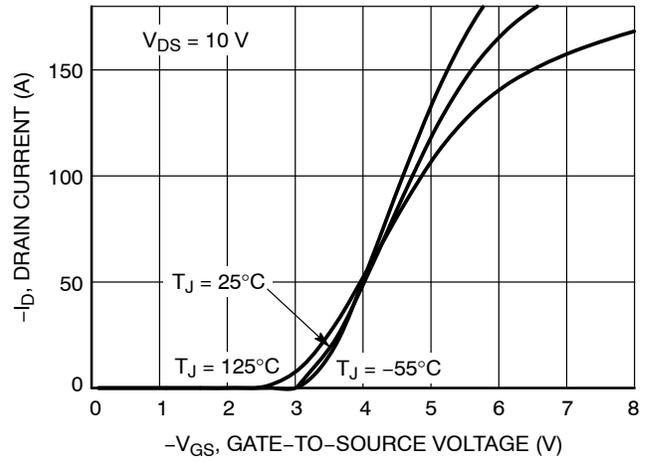


Figure 2. Transfer Characteristics

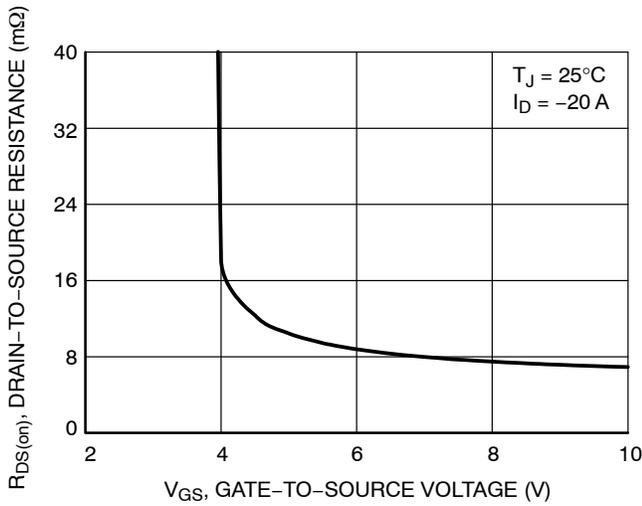


Figure 3. On-Resistance vs. Gate-to-Source Voltage

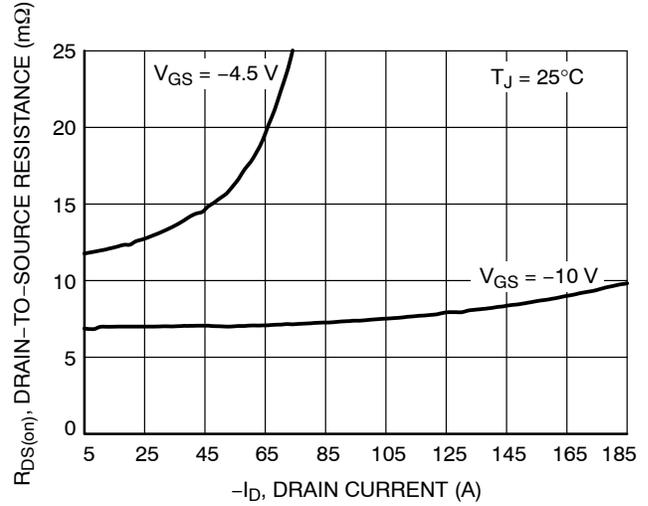


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

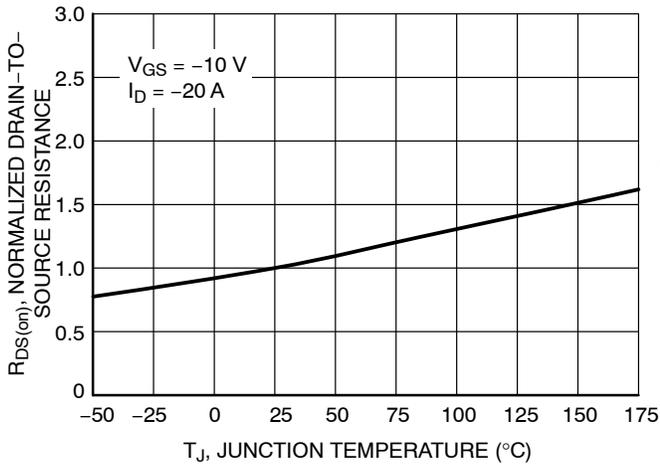


Figure 5. On-Resistance Variation with Temperature

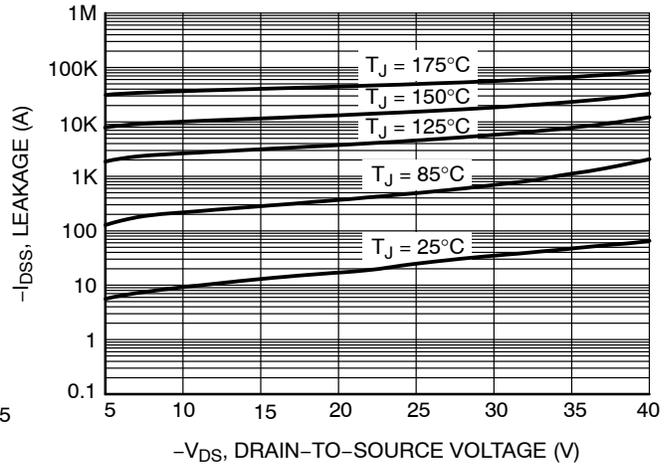


Figure 6. Drain-to-Source Leakage Current vs. Voltage

# NVMFS9D6P04M8L

## TYPICAL CHARACTERISTICS

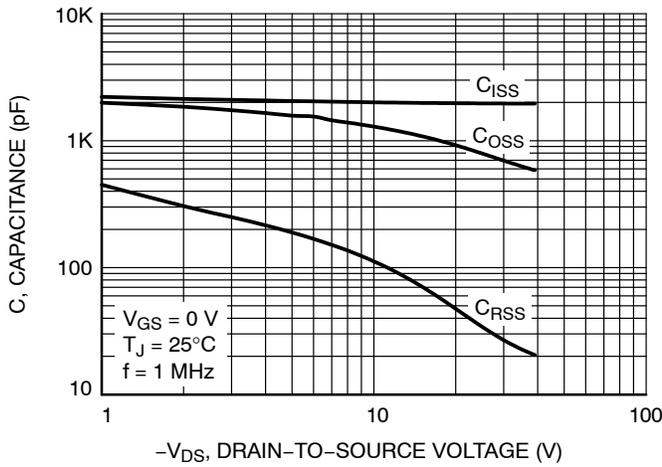


Figure 7. Capacitance Variation

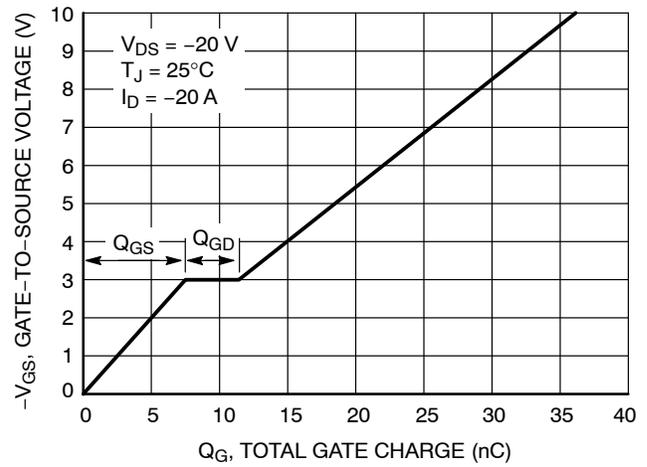


Figure 8. Gate-to-Source vs. Total Charge

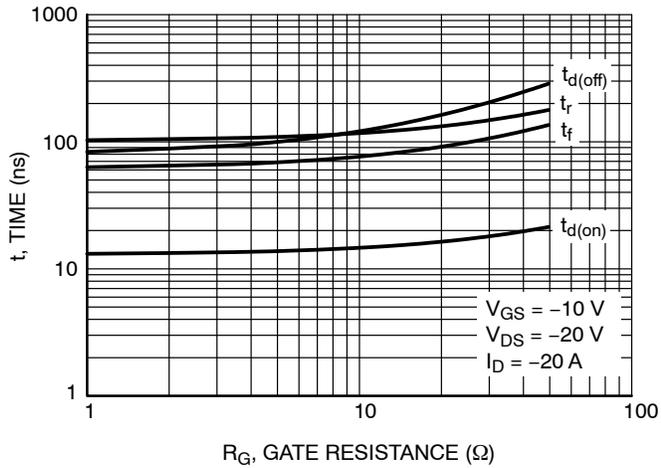


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

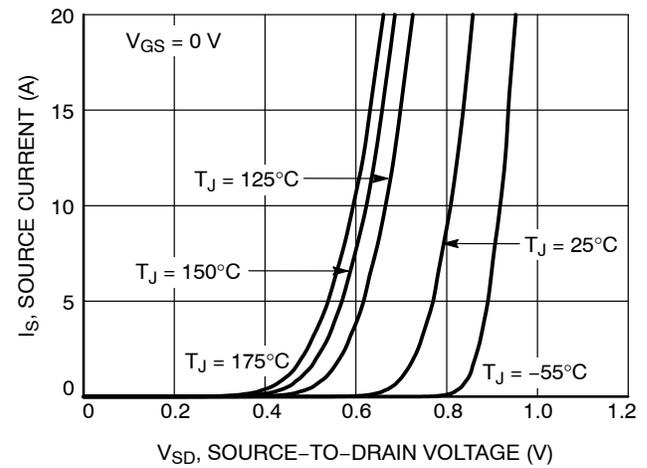


Figure 10. Diode Forward Voltage vs. Current

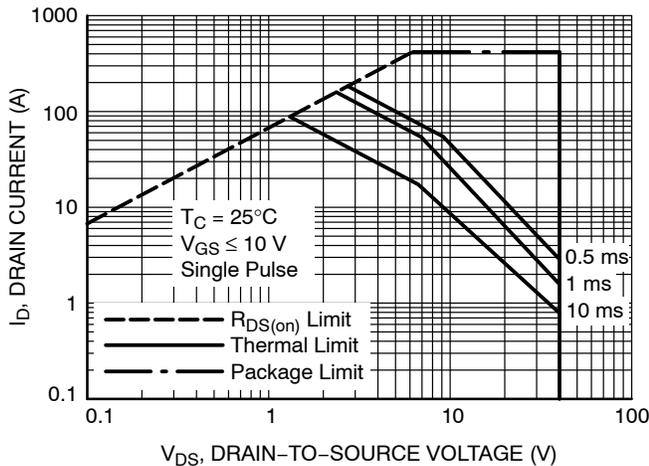


Figure 11. Maximum Rated Forward Biased Safe Operating Area

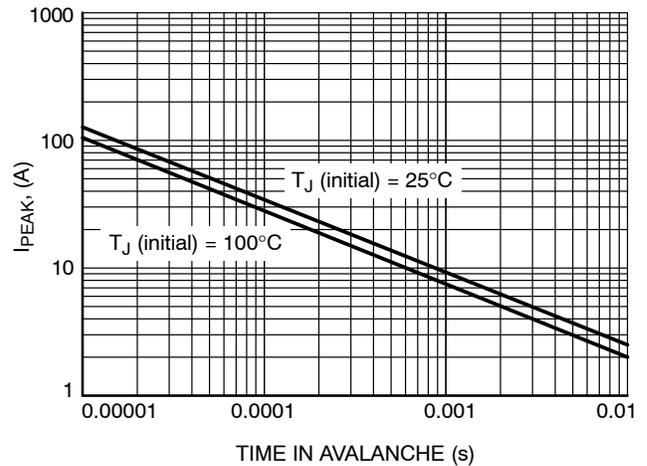


Figure 12.  $I_{PEAK}$  vs. Time in Avalanche

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## TYPICAL CHARACTERISTICS

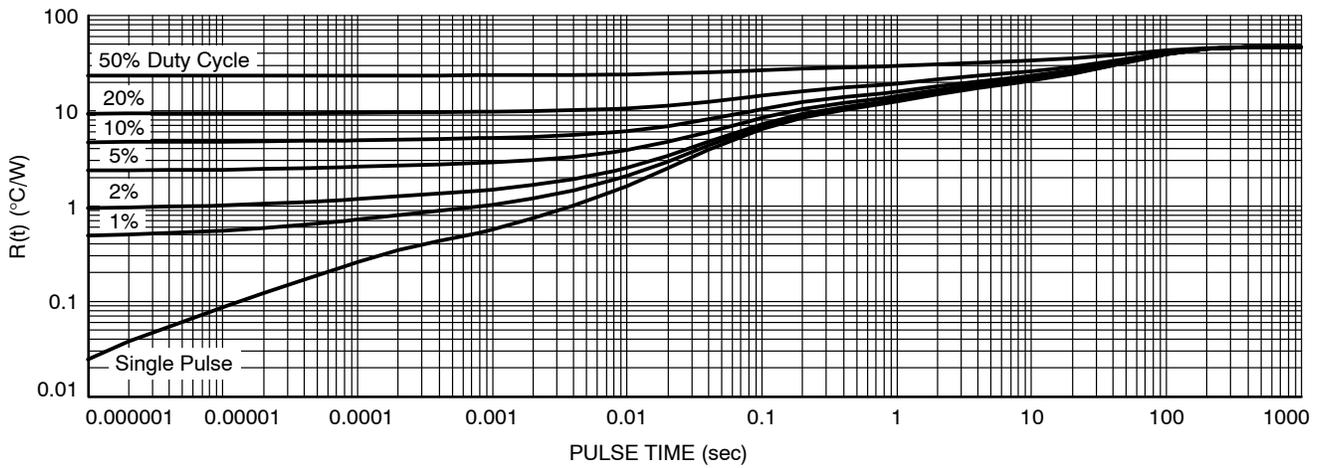


Figure 13. Thermal Characteristics

### DEVICE ORDERING INFORMATION

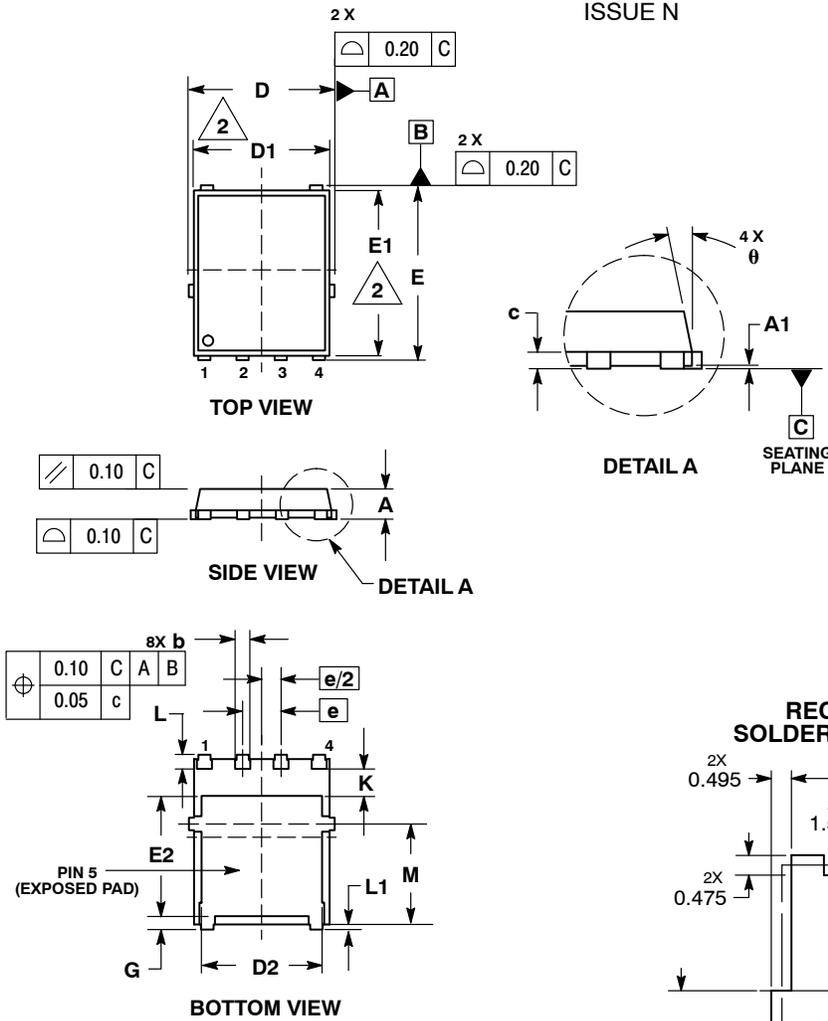
Device	Marking	Package	Shipping <sup>†</sup>
NVMFS9D6P04M8LT1G	V9D6PL	DFNW5 (Pb-Free)	1500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NVMFS9D6P04M8L

## PACKAGE DIMENSIONS

DFN5 5x6, 1.27P  
(SO-8FL)  
CASE 488AA  
ISSUE N



### NOTES:

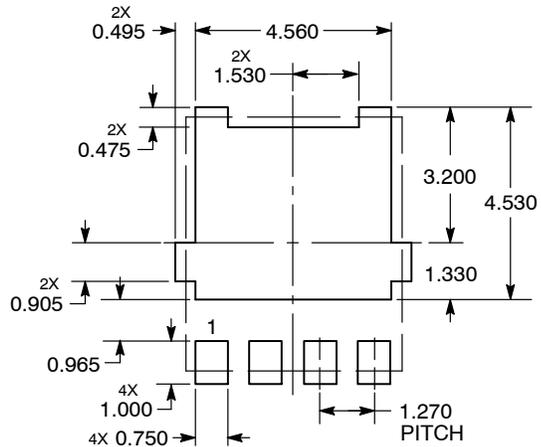
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

### STYLE 1:

1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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